

# 深圳市晶泰源电子有限公司

8050C

TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	40	V
VCEO	Collector-Emitter Voltage	25	V
VEBO	Emitter-Base Voltage	5	V
IC	Collector Current	0.5	A
PC	Collector Power Dissipation	625	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C

T0-92

1. EMITTER

2. BASE

3. COLLECTOR



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	25			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	5			V
Collector cut-off current	ICBO	VCE=40V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=5V, IC=0			0.1	μA
DC current gain	HFE	Vce=1V, IC=50mA	120		200	
Collector-emitter saturation voltage	VCE(sat)	IC=500mA, IB=50mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=500mA, IB=50mA			1.2	V
Base-emitter voltage	VBE	VCE=1V, IC=10mA			1.0	V
Transition frequency	fT	VCE=6V, IC=20mA, f=30MHZ	150			MHz

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